TECHNICAL DATA DATA SHEET 786, REV. C

## SILICON SCHOTTKY RECTIFIER Very Low Forward Voltage Drop

#### Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Excellent Reverse Avalanche Characteristics

#### **Maximum Ratings**

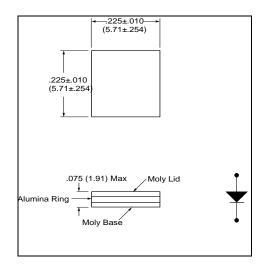
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	60	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle, rectangular	30	Α
Current		wave form		
Max. Peak One Cycle Non-	I <sub>FSM</sub>	8.3 ms, half Sine wave	280	Α
Repetitive Surge Current				
Non-Repetitive Avalanche	$E_AS$	$T_J = 25  ^{\circ}\text{C}, I_{AS} = 11.5  \text{A},$	13 (typ)	mJ
Energy		L = 11.5 mH		
Repetitive Avalanche Current	$I_{AR}$	I <sub>AS</sub> decay linearly to 0 in 1 μs	1.5	Α
		f limited by T <sub>J</sub> max V <sub>A</sub> =1.5V <sub>R</sub>		
Maximum Thermal Resistance	$R_{ hetaJC}$		1.7	°C/W
Maximum mornia redictario	I V <sub>θ</sub> JC		1.7	0/11
Max. Junction Temperature	$T_J$	-	-55 to +150	°C
Max. Storage Temperature	$T_{stg}$	-	-55 to +150	°C

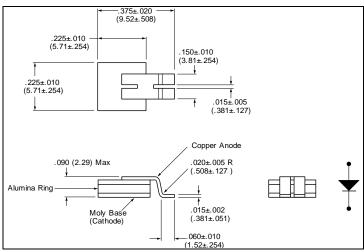
### **Electrical Characteristics**

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	$V_{F1}$	@ 15A, Pulse, T <sub>J</sub> = 25 °C	0.60	V
	$V_{F2}$	@ 15A, Pulse, T <sub>J</sub> = 125 °C	0.56	V
Max. Reverse Current	I <sub>R1</sub>	@V <sub>R</sub> = 60V, Pulse,	0.8	mA
		T <sub>J</sub> = 25 °C		
	I <sub>R2</sub>	$@V_R = 60V$ , Pulse,	45	mA
		T <sub>J</sub> = 125 °C		
Max. Junction Capacitance	C <sub>T</sub>	$@V_R = 5V, T_C = 25  ^{\circ}C$	720	pF
		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV (p-p)}$		

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#### **MECHANICAL DIMENSIONS: In Inches / mm**



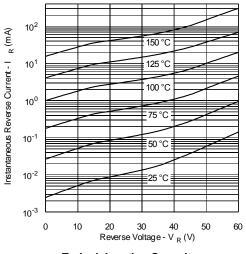


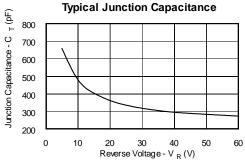
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#### Typical Reverse Characteristics





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